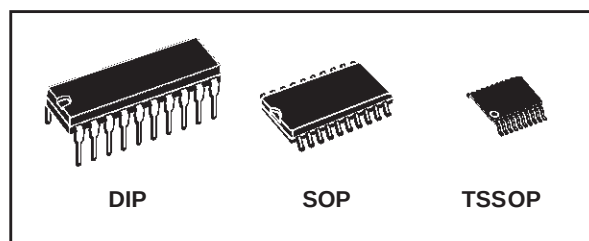




M74HC7244

OCTAL BUS BUFFER WITH 3 STATE OUTPUTS (NON INVERTED)

- HIGH SPEED:
 $t_{PD} = 13ns$ (TYP.) at $V_{CC} = 6V$
- LOW POWER DISSIPATION:
 $I_{CC} = 4\mu A$ (MAX.) at $T_A = 25^\circ C$
- HIGH NOISE IMMUNITY:
 $V_H = 1.2 V$ (TYP.) at $V_{CC} = 6V$
- SYMMETRICAL OUTPUT IMPEDANCE:
 $|I_{OH}| = I_{OL} = 6mA$ (MIN)
- BALANCED PROPAGATION DELAYS:
 $t_{PLH} \approx t_{PHL}$
- WIDE OPERATING VOLTAGE RANGE:
 V_{CC} (OPR) = 2V to 6V
- PIN AND FUNCTION COMPATIBLE WITH
74 SERIES 7244



ORDER CODES

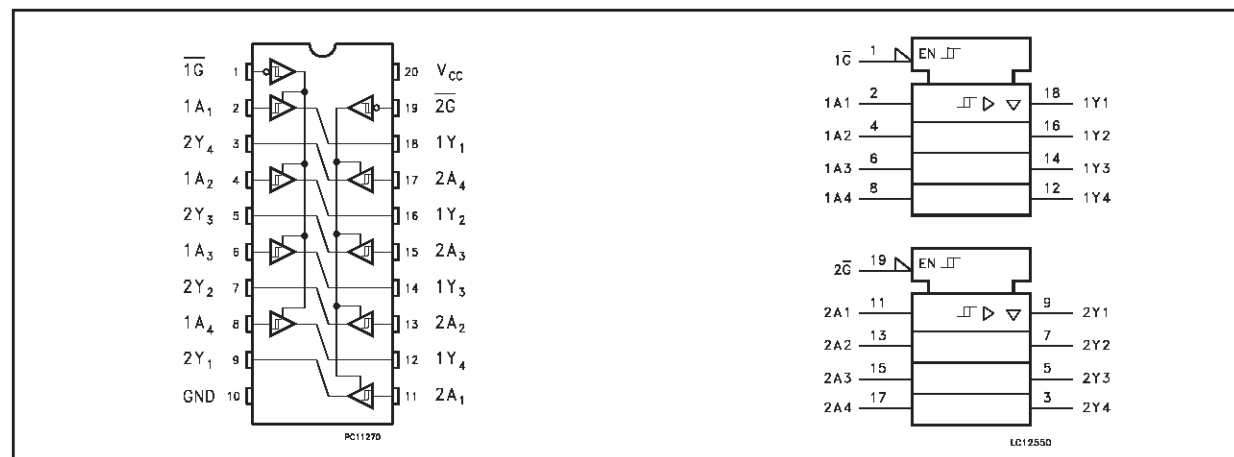
PACKAGE	TUBE	T & R
DIP	M74HC7244B1R	
SOP	M74HC7244M1R	M74HC7244RM13TR
TSSOP		M74HC7244TTR

DESCRIPTION

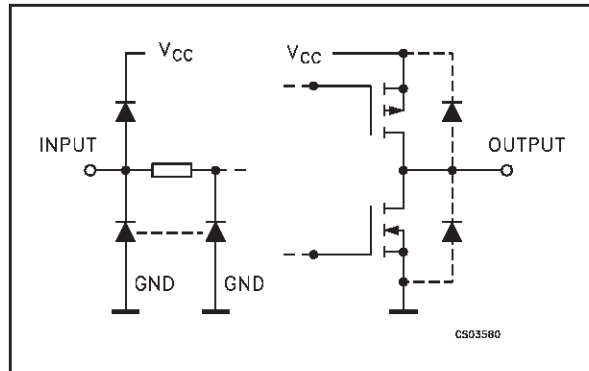
The 74HC7244 is an advanced high-speed CMOS OCTAL BUS BUFFER (3-STATE) fabricated with silicon gate C²MOS technology.
 $\overline{G}$ control input governs four BUS BUFFERS.

This device have a hysteresis characteristics with each input so can be used as a line receiver, etc. All inputs are equipped with protection circuits against static discharge and transient excess voltage.

PIN CONNECTION AND IEC LOGIC SYMBOLS



INPUT AND OUTPUT EQUIVALENT CIRCUIT



PIN DESCRIPTION

PIN No	SYMBOL	NAME AND FUNCTION
1	$\overline{1G}$	Output Enable Input
2, 4, 6, 8	1A1 to 1A4	Data Inputs
9, 7, 5, 3	2Y1 to 2Y4	Data Outputs
11, 13, 15, 17	2A1 to 2A4	Data Inputs
18, 16, 14, 12	1Y1 to 1Y4	Data Outputs
19	$\overline{2G}$	Output Enable Input
10	GND	Ground (0V)
20	V_{CC}	Positive Supply Voltage

TRUTH TABLE

INPUTS		OUTPUT
$\overline{G}$	A_n	Y_n
L	L	L
L	H	H
H	X	Z

X : Don't Care
Z : High Impedance

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CC}	Supply Voltage	-0.5 to +7	V
V_I	DC Input Voltage	-0.5 to $V_{CC} + 0.5$	V
V_O	DC Output Voltage	-0.5 to $V_{CC} + 0.5$	V
I_{IK}	DC Input Diode Current	± 20	mA
I_{OK}	DC Output Diode Current	± 20	mA
I_O	DC Output Current	± 35	mA
I_{CC} or I_{GND}	DC V_{CC} or Ground Current	± 70	mA
P_D	Power Dissipation	500(*)	mW
T_{stg}	Storage Temperature	-65 to +150	°C
T_L	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied.

(*) 500mW at 65 °C; derate to 300mW by 10mW/°C from 65°C to 85°C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V_{CC}	Supply Voltage	2 to 6	V
V_I	Input Voltage	0 to V_{CC}	V
V_O	Output Voltage	0 to V_{CC}	V
T_{op}	Operating Temperature	-55 to 125	°C

DC SPECIFICATIONS

Symbol	Parameter	Test Condition		Value							Unit
		V _{CC} (V)		T _A = 25°C			-40 to 85°C		-55 to 125°C		
				Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
V _P	High Level Threshold Voltage	2.0		1.0	1.25	1.5	1.0	1.5	1.0	1.5	V
		4.5		2.3	2.7	3.15	2.3	3.15	2.3	3.15	
		6.0		3.0	3.5	4.2	3.0	4.2	3.0	4.2	
V _N	Low Level Threshold Voltage	2.0		0.3	0.65	0.9	0.3	0.9	0.3	0.9	V
		4.5		1.13	1.6	2.0	1.13	2.0	1.13	2.0	
		6.0		1.5	2.3	2.6	1.5	2.6	1.5	2.6	
V _H	Hysteresis Voltage	2.0		0.3	0.6	1.0	0.3	1.0	0.3	1.0	V
		4.5		0.6	1.1	1.4	0.6	1.4	0.6	1.4	
		6.0		0.8	1.2	1.7	0.8	1.7	0.8	1.7	
V _{OH}	High Level Output Voltage	2.0	I _O =-20 μA	1.9	2.0		1.9		1.9		V
		4.5	I _O =-20 μA	4.4	4.5		4.4		4.4		
		6.0	I _O =-20 μA	5.9	6.0		5.9		5.9		
		4.5	I _O =-6.0 mA	4.18	4.31		4.13		4.10		
		6.0	I _O =-7.8 mA	5.68	5.8		5.63		5.60		
V _{OL}	Low Level Output Voltage	2.0	I _O =20 μA		0.0	0.1		0.1		0.1	V
		4.5	I _O =20 μA		0.0	0.1		0.1		0.1	
		6.0	I _O =20 μA		0.0	0.1		0.1		0.1	
		4.5	I _O =6.0 mA		0.17	0.26		0.33		0.40	
		6.0	I _O =7.8 mA		0.18	0.26		0.33		0.40	
I _I	Input Leakage Current	6.0	V _I = V _{IH} or V _{IL} V _O = V _{CC} or GND			± 0.1		± 1		± 1	μA
I _{OZ}	High Impedance Output Leakage Current	6.0	V _I = V _{CC} or GND			± 0.5		± 5		± 10	μA
I _{CC}	Quiescent Supply Current	6.0	V _I = V _{CC} or GND			4		40		80	μA

AC ELECTRICAL CHARACTERISTICS ($C_L = 50 \text{ pF}$, Input $t_r = t_f = 6 \text{ ns}$)

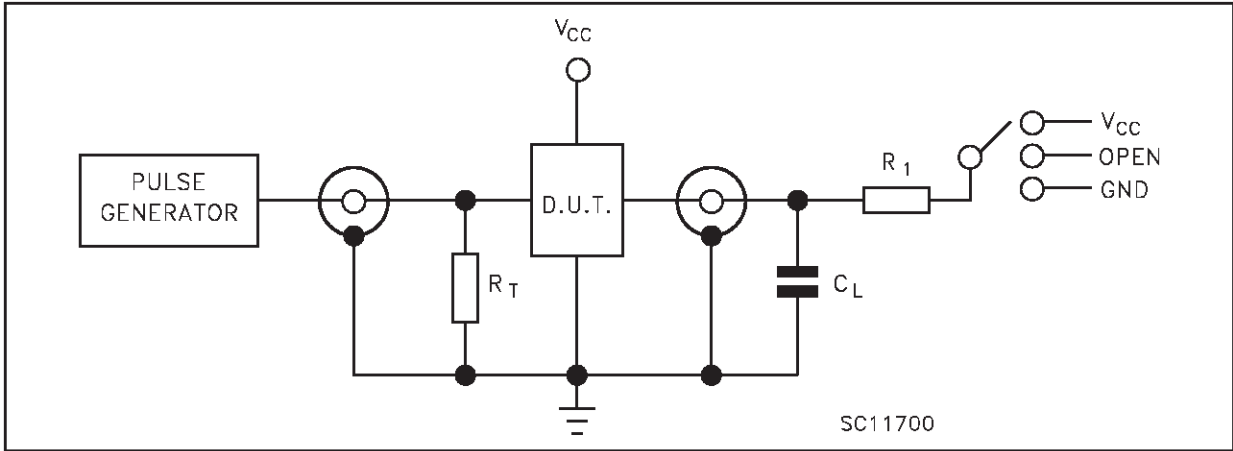
Symbol	Parameter	Test Condition			Value							Unit
		V _{CC} (V)	C _L (pF)		T _A = 25°C			-40 to 85°C		-55 to 125°C		
					Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
t _{TLH} t _{THL}	Output Transition Time	2.0	50			25	60		75			ns
		4.5				7	12		19			
		6.0				6	10		13			
t _{PLH} t _{PHL}	Propagation Delay Time	2.0	50			50	125		155			ns
		4.5				15	25		31			
		6.0				13	21		26			
t _{PZL} t _{PZH}	High Impedance Output Enable Time	2.0	50	R _L = 1 KΩ		68	150		190			ns
		4.5				21	30		38			
		6.0				16	26		32			
t _{PLZ} t _{PHZ}	High Impedance Output Disable Time	2.0	50	R _L = 1 KΩ		48	150		190			ns
		4.5				21	30		38			
		6.0				19	26		32			

CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Test Condition			Value						Unit	
		V _{CC} (V)			T _A = 25°C			-40 to 85°C		-55 to 125°C		
					Min.	Typ.	Max.	Min.	Max.	Min.		Max.
C _{IN}	Input Capacitance	5.0				5	10		10		10	pF
C _{OUT}	Output Capacitance	5.0				10						pF
C _{PD}	Power Dissipation Capacitance (note 1)	5.0				34						pF

1) C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation. $I_{CC(opr)} = C_{PD} \times V_{CC} \times f_{IN} + I_{CC}/8$ (per circuit)

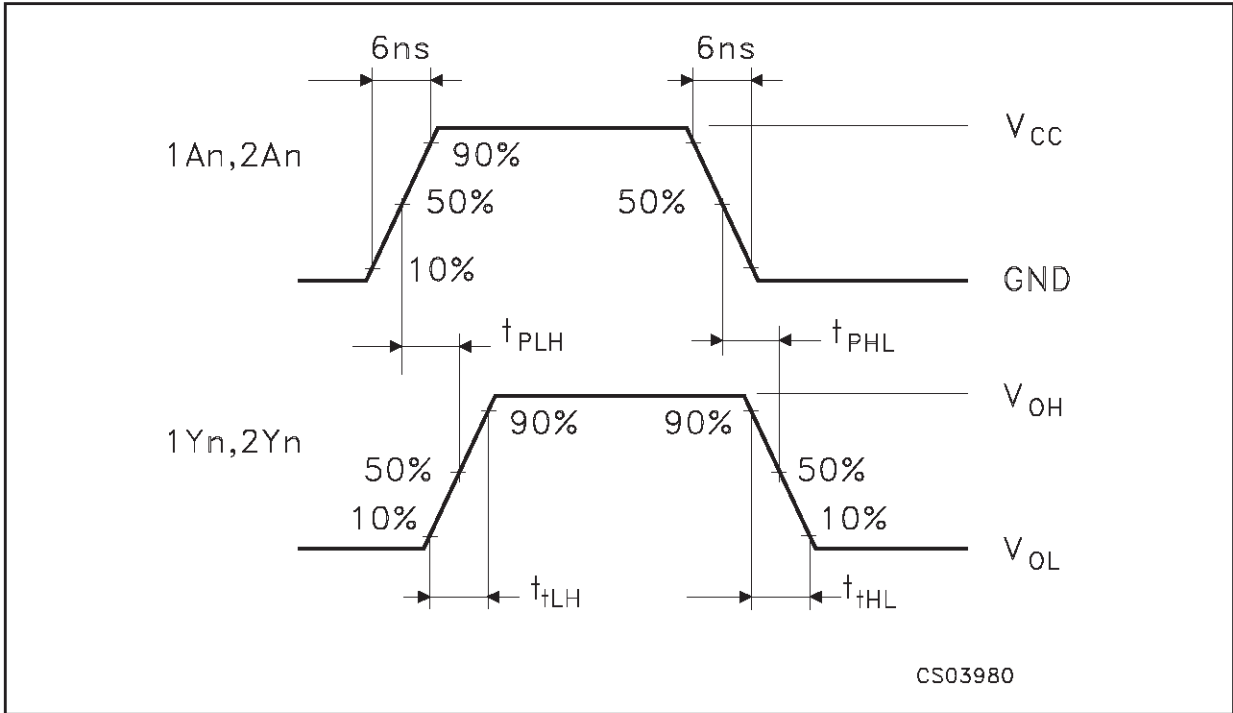
TEST CIRCUIT



TEST	SWITCH
t_{PLH} , t_{PHL}	Open
t_{PZL} , t_{PLZ}	V_{CC}
t_{PZH} , t_{PHZ}	GND

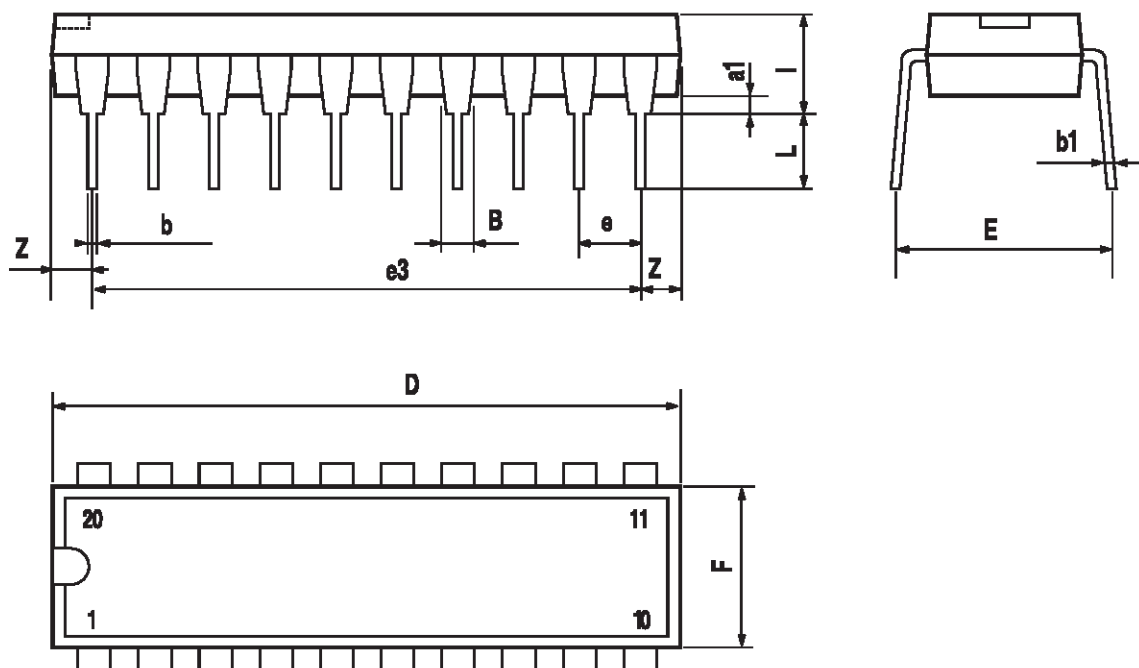
C_L = 50pF/150pF or equivalent (includes jig and probe capacitance)
 R_1 = 1K Ω or equivalent
 R_T = Z_{OUT} of pulse generator (typically 50 Ω)

WAVEFORM 1: PROPAGATION DELAY TIME (f=1MHz; 50% duty cycle)



Plastic DIP-20 (0.25) MECHANICAL DATA

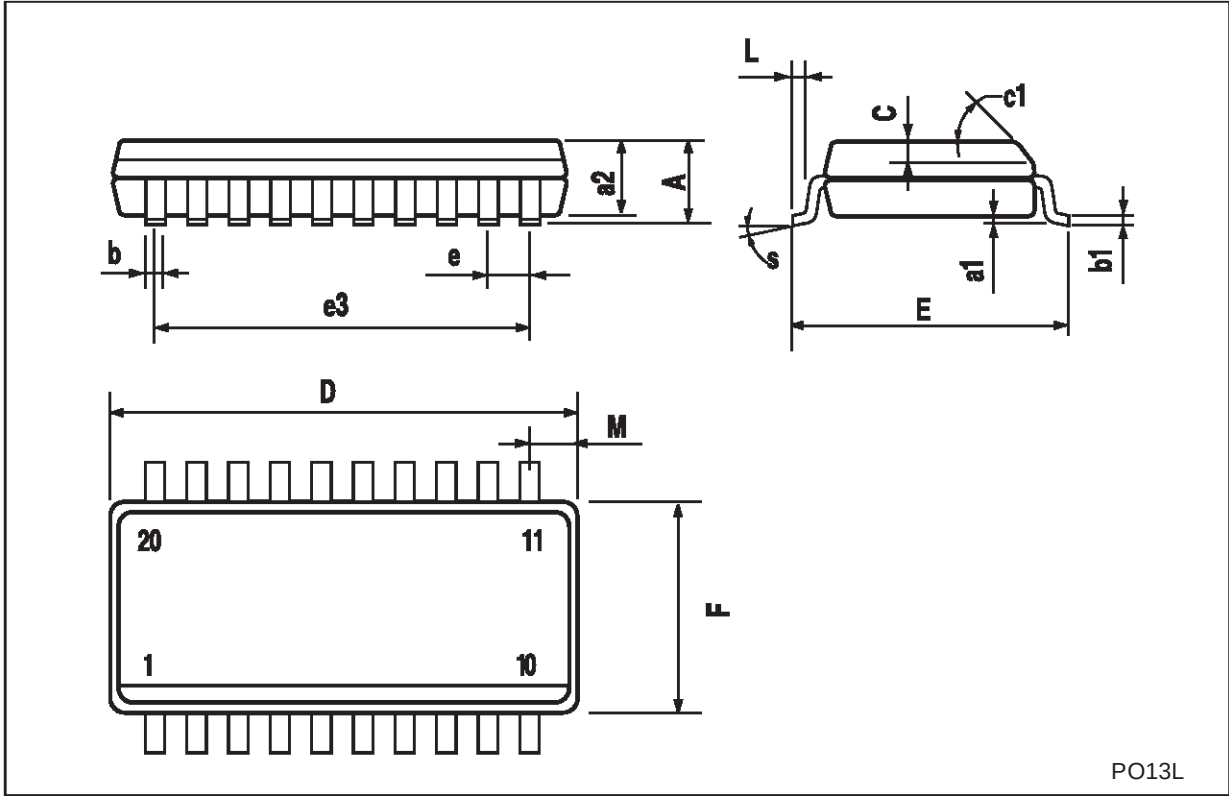
DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
a1	0.254			0.010		
B	1.39		1.65	0.055		0.065
b		0.45			0.018	
b1		0.25			0.010	
D			25.4			1.000
E		8.5			0.335	
e		2.54			0.100	
e3		22.86			0.900	
F			7.1			0.280
I			3.93			0.155
L		3.3			0.130	
Z			1.34			0.053



P001J

SO-20 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A			2.65			0.104
a1	0.1		0.2	0.004		0.008
a2			2.45			0.096
b	0.35		0.49	0.014		0.019
b1	0.23		0.32	0.009		0.012
C		0.5			0.020	
c1	45° (typ.)					
D	12.60		13.00	0.496		0.512
E	10.00		10.65	0.393		0.419
e		1.27			0.050	
e3		11.43			0.450	
F	7.40		7.60	0.291		0.300
L	0.50		1.27	0.020		0.050
M			0.75			0.029
S	8° (max.)					

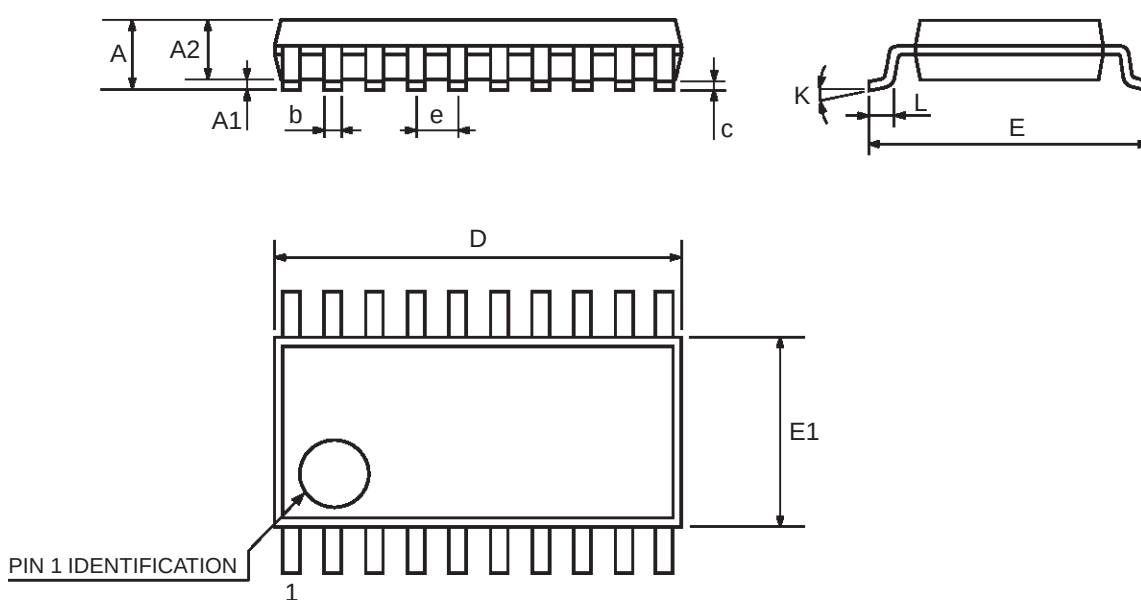


PO13L



TSSOP20 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A			1.2			0.047
A1	0.05		0.15	0.002	0.004	0.006
A2	0.8	1	1.05	0.031	0.039	0.041
b	0.19		0.30	0.007		0.012
c	0.09		0.20	0.004		0.0089
D	6.4	6.5	6.6	0.252	0.256	0.260
E	6.2	6.4	6.6	0.244	0.252	0.260
E1	4.3	4.4	4.48	0.169	0.173	0.176
e		0.65 BSC			0.0256 BSC	
K	0°		8°	0°		8°
L	0.45	0.60	0.75	0.018	0.024	0.030



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